NSN 5961-01-219-6427

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-219-6427 **Inclosure Material:** Metal **Overall Length:** 1.735 inches **Mounting Facility Quantity: Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.559 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 250.00 amperes peak forward surge current nanoamperes **Power Rating Per Characteristic:** 20.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Test Data Document:** 96214-2690662 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0